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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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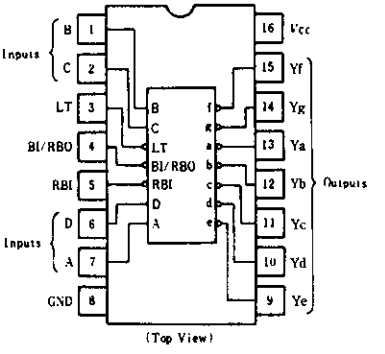
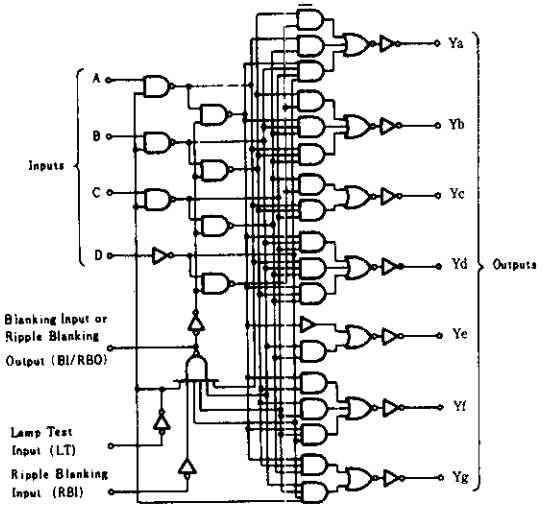
HD74LS47 ●BCD-to-Seven-Segment Decoder/Driver (with 15V Outputs)

HD74LS47 features active-low outputs designed for driving incandescent indicators directly. This device has full ripple-blanking input/output controls and a lamp test input. Display patterns for BCD input counts above 9 are unique symbols to authenticate input conditions. This circuit incorporates automatic leading and/or tailling-edge zero-blanking control (RBI and RBO). Lamp test (LT) of these types may be performed at any time when the BI/RBO node is at a high level. It contains an overriding blanking input (BI) which can be used to control the lamp intensity of pulsing or to inhibit the outputs. Inputs and outputs are entirely compatible for use with TTL or DTL logic outputs.

■PIN ARRANGEMENT



■BLOCK DIAGRAM



■ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Ratings	Unit
Supply voltage	V_{CC}	7.0	V
Input voltage	V_{IN}	7.0	V
Output current ($t_W \leqq 1$ms, duty cycle $\leqq 10\%$)	$I_{O(peak)}$	200	mA
Output current (off-state)	$I_{O(off)}$	1	mA
Operating temperature range	T_{opr}	−20 ~ +75	℃
Storage temperature range	T_{stg}	−65 ~ +150	℃

■FUNCTION TABLE

Decimal or Function	Inputs						BI/RBO	Outputs							Note
	LT	RBI	D	C	B	A		a	b	c	d	e	f	g	
0	H	H	L	L	L	L	H	ON	ON	ON	ON	ON	ON	OFF	1
1	H	×	L	L	L	H	H	OFF	ON	ON	OFF	OFF	OFF	OFF	
2	H	×	L	L	H	L	H	ON	ON	OFF	ON	ON	OFF	ON	
3	H	×	L	L	H	H	H	ON	ON	ON	ON	OFF	OFF	ON	
4	H	×	L	H	L	L	H	OFF	ON	ON	OFF	OFF	ON	ON	
5	H	×	L	H	L	H	H	ON	OFF	ON	ON	OFF	ON	ON	
6	H	×	L	H	H	L	H	OFF	OFF	ON	ON	ON	ON	ON	
7	H	×	L	H	H	H	H	ON	ON	ON	OFF	OFF	OFF	OFF	
8	H	×	H	L	L	L	H	ON	ON	ON	ON	ON	ON	ON	
9	H	×	H	L	L	H	H	ON	ON	ON	OFF	OFF	ON	ON	
10	H	×	H	L	H	L	H	OFF	OFF	OFF	ON	ON	OFF	ON	
11	H	×	H	L	H	H	H	OFF	OFF	ON	ON	OFF	OFF	ON	
12	H	×	H	H	L	L	H	OFF	ON	OFF	OFF	OFF	ON	ON	
13	H	×	H	H	L	H	H	ON	OFF	OFF	ON	OFF	ON	ON	
14	H	×	H	H	H	L	H	OFF	OFF	OFF	ON	ON	ON	ON	
15	H	×	H	H	H	H	H	OFF	OFF	OFF	OFF	OFF	OFF	OFF	
BI	×	×	×	×	×	×	L	OFF	OFF	OFF	OFF	OFF	OFF	OFF	2
RBI	H	L	L	L	L	L	L	OFF	OFF	OFF	OFF	OFF	OFF	OFF	3
LT	L	×	×	×	×	×	H	ON	ON	ON	ON	ON	ON	ON	4

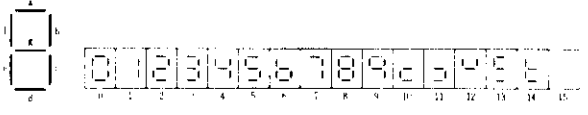
H; high level, L; low level, X; irrelevant

Notes: 1. The blanking input (BI) must be open or held at a high logic level when output functions 0 through 15 are desired. The ripple-blanking input (RBI) must be open or high if blanking of a decimal zero is not desired.

2. When a low logic level is applied directly to the blanking input (BI), all segment outputs are off regardless of the level of any other input.

3. When ripple-blanking input (RBI) and inputs A, B, C, and D are a low level with the lamp test input high, all segment outputs go off and the ripple-blanking output (RBO) goes to a low level (response condition).

4. When a blanking input/ripple blanking output (BI/RBO) is open or held high and a low is applied to the lamp-test input, all segment outputs are on.



■RECOMMENDED OPERATING CONDITIONS

Item	Symbol	min	typ	max	Unit
Supply voltage	V_{CC}	4.75	5.0	5.25	V
Off-state output voltage *	$V_{O(off)}$			15	V
On-state output current *	$I_{O(on)}$			24	mA
High level output current **	I_{OH}			−50	μA
Low level output current **	I_{OL}			3.2	mA
Operating temperature range	T_{opr}	−20	25	75	°C

* Applied to the a through g outputs.
** BI/RBO terminal.

■ELECTRICAL CHARACTERISTICS (Ta= −20 ~ +75°C)

Item		Symbol	Test Conditions		min	typ*	max	Unit
Input voltage		V_{IH}			2.0	–	–	V
		V_{IL}			–	–	0.8	V
Output voltage	BI/RBO	V_{OH}	V_{CC}=4.75V, V_{IH}=2V, V_{IL}=0.8V, I_{OH}=−50μA		2.4	–	–	V
		V_{OL}	V_{CC}=4.75V, V_{IH}=2V, V_{IL}=0.8V	I_{OL}=1.6mA	–	–	0.4	V
				I_{OL}=3.2mA	–	–	0.5	V
	a ~ g	$V_{O(on)}$	V_{CC}=5.25V, V_{IH}=2V, V_{IL}=0.8V	$I_{O(on)}$=12mA	–	–	0.4	V
				$I_{O(on)}$=24mA	–	–	0.5	V
Output current	a ~ g	$I_{O(off)}$	V_{CC}=5.25V, V_{IH}=2V, V_{IL}=0.8V, $V_{O(off)}$=15V		–	–	250	μA
Input current	All input except BI/RBO	I_{IH}	V_{CC}=5.25V, V_I=2.7V		–	–	20	μA
		I_{IL}	V_{CC}=5.25V, V_I=0.4V		–	–	−0.4	mA
	BI/RBO				–	–	−1.2	mA
		I_I	V_{CC}=5.25V, V_I=7V		–	–	0.1	mA
Short-circuit output current	BI/RBO	I_{OS}	V_{CC}=5.25V		−0.3	–	−2	mA
Supply current **		I_{CC}	V_{CC}=5.25V		–	7	13	mA
Input clamp voltage		V_{IK}	V_{CC}=4.75V, I_{IN}=−18mA		–	–	−1.5	V

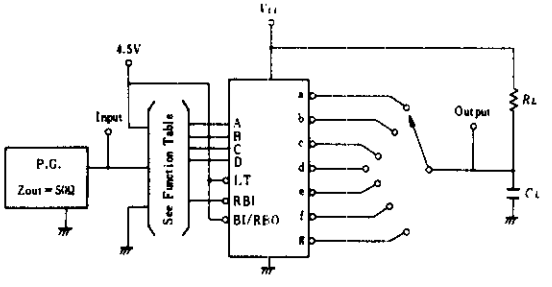
* V_{CC}=5V, Ta=25°C
** I_{CC} is measured with all outputs open and all inputs at 4.5V.

■SWITCHING CHARACTERISTICS (V_{CC}=5V, Ta=25°C)

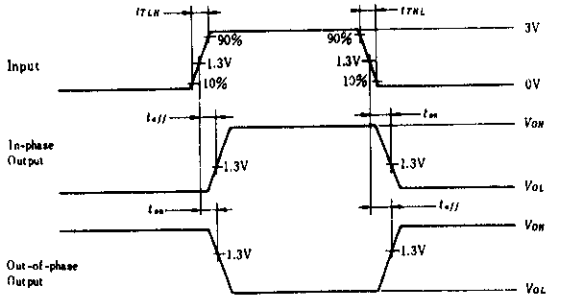
Item	Symbol	Input	Test Conditions	min	typ	max	Unit
Turn-on time	t_{on}	A	C_L=15pF, R_L=665Ω	–	–	100	ns
		RBI		–	–	100	ns
Turn-off time	t_{off}	A		–	–	100	ns
		RBI		–	–	100	ns

■TESTING METHOD

1) Test Circuit



Waveform

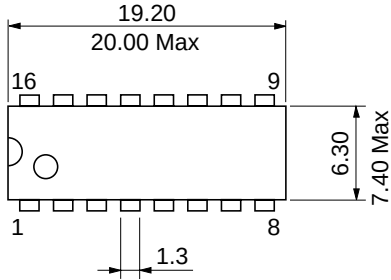


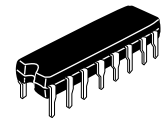
2) Testing Table

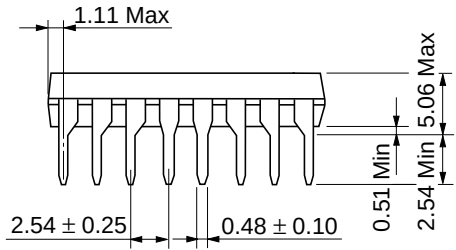
Item	Inputs					Outputs						
	RBI	D	C	B	A	a	b	c	d	e	f	g
	4.5V	GND	GND	GND	IN	OUT	–	–	OUT	OUT	OUT	–
t_{on}	4.5V	GND	GND	4.5V	IN	–	–	OUT	–	OUT	–	–
t_{off}	4.5V	GND	4.5V	4.5V	IN	OUT	OUT	–	OUT	OUT	OUT	OUT
	IN	GND	GND	GND	GND	OUT	OUT	OUT	OUT	OUT	OUT	–

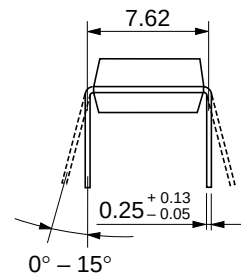
Input pulse; $t_{TLH} \leqq 15$ns, $t_{THL} \leqq 6$ns, PRR=1MHz, duty cycle 50%.

Unit: mm



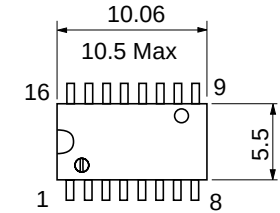


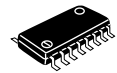


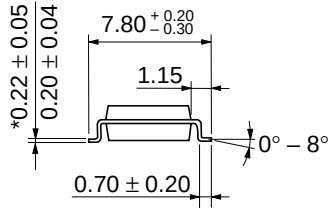


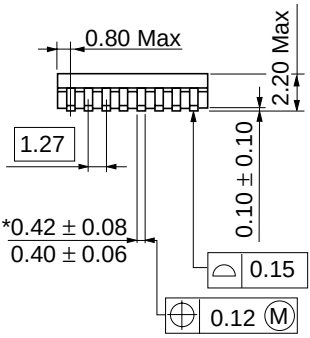
Hitachi Code	DP-16
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.07 g

Unit: mm





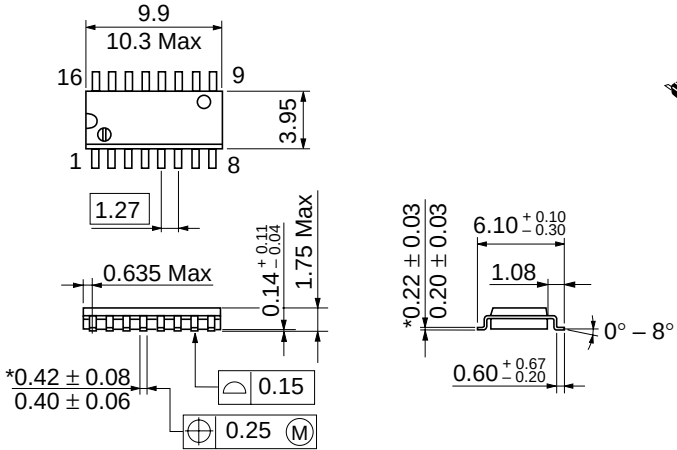


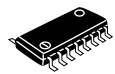


*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.24 g

Unit: mm





Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.15 g

*Dimension including the plating thickness
Base material dimension

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